



Amorphous oxide semiconductors (AOSs) are emerging as promising materials for the active layers of thin film transistors (TFTs), which are used in active-matrix liquid crystal display (AMLCD) and active

Experimental

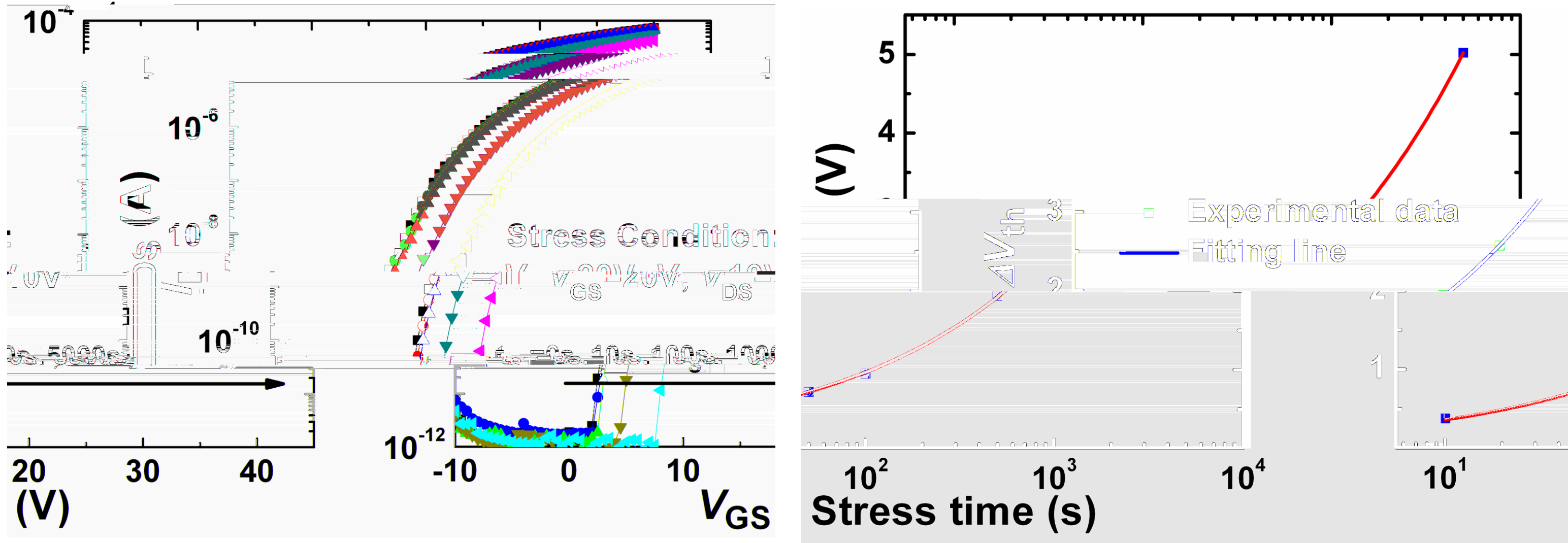
The channel layer deposition:

- Via PLD (10Hz; 300 mJ)
- Ceramic target
- Room temperature
- Oxygen partial pressure: 6.7 Pa
- Substrate-target distance: 4.5 ~ 6 cm
- Thickness: 50 nm
- Annealing at 400 ℃ in air

Fig. 2. Schematic of an *a*-InGaZnO TFT in a bottom-gate coplanar configuration.

Results and discussion

B. Stability of annealed *a*-InGaZnO TFTs



Conclusions